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Studies of GaInP based Geiger-mode APD arrays

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Devices composed of wide band gap semiconductors such as GaInP have the theoretical potential to withstand many orders of magnitude larger radiation exposures compared to silicon. LightSpin Technologies has developed high density, large area SPAD arrays in GaInP with resolution for single photon peaks over the past several years. We report on measurements

using a sample of the latest generation of prototype devices, demonstrating performance properties of new large GAPD arrays based on this compound semiconductor.

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